

V_{CES}	650V
$I_{C(100^{\circ}C)}$	40A
$V_{CE(sat)} (Typ.)$	1.6V
P_D	234W

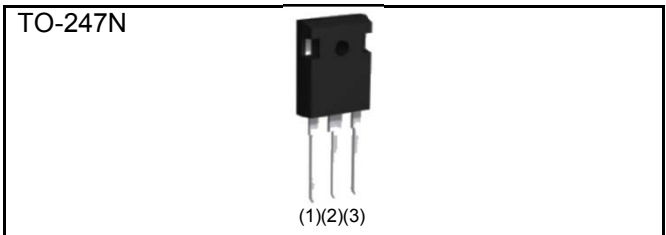
●Features

- 1) Low Collector - Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD (RFN - Series)
- 5) Pb - free Lead Plating ; RoHS Compliant

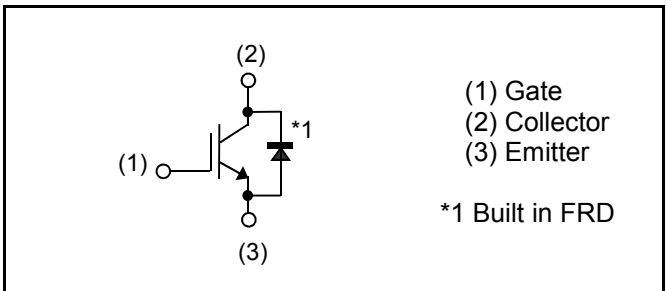
●Applications

PFC
UPS
Power Conditioner
IH

●Outline



●Inner Circuit



●Packaging Specifications

Type	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH80TS65D

●Absolute Maximum Ratings (at $T_C = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Value	Unit	
Collector - Emitter Voltage	V_{CES}	650	V	
Gate - Emitter Voltage	V_{GES}	± 30	V	
Collector Current	$T_C = 25^{\circ}C$	I_C	70	A
	$T_C = 100^{\circ}C$	I_C	40	A
Pulsed Collector Current	I_{CP}^{*1}	160	A	
Diode Forward Current	$T_C = 25^{\circ}C$	I_F	40	A
	$T_C = 100^{\circ}C$	I_F	20	A
Diode Pulsed Forward Current	I_{FP}^{*1}	160	A	
Power Dissipation	$T_C = 25^{\circ}C$	P_D	234	W
	$T_C = 100^{\circ}C$	P_D	117	W
Operating Junction Temperature	T_j	-40 to +175	$^{\circ}C$	
Storage Temperature	T_{stg}	-55 to +175	$^{\circ}C$	

*1 Pulse width limited by T_{jmax} .

● Thermal Resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.64	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.00	°C/W

● IGBT Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector - Emitter Breakdown Voltage	BV_{CES}	$I_C = 10\mu\text{A}, V_{GE} = 0\text{V}$	650	-	-	V
Collector Cut - off Current	I_{CES}	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$	-	-	10	μA
Gate - Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 30\text{V}, V_{CE} = 0\text{V}$	-	-	± 200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5\text{V}, I_C = 27.6\text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}$	-	1.6	2.1	V
		$T_j = 25^\circ\text{C}$	-	2.1	-	
		$T_j = 175^\circ\text{C}$	-			

●IGBT Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{ies}	$V_{CE} = 30\text{V}$	-	2210	-	pF
Output Capacitance	C_{oes}	$V_{GE} = 0\text{V}$	-	85	-	
Reverse Transfer Capacitance	C_{res}	$f = 1\text{MHz}$	-	35	-	
Total Gate Charge	Q_g	$V_{CE} = 300\text{V}$	-	79	-	nC
Gate - Emitter Charge	Q_{ge}	$I_C = 40\text{A}$	-	21	-	
Gate - Collector Charge	Q_{gc}	$V_{GE} = 15\text{V}$	-	29	-	
Turn - on Delay Time	$t_{d(on)}$	$I_C = 40\text{A}, V_{CC} = 400\text{V}$	-	34	-	ns
Rise Time	t_r	$V_{GE} = 15\text{V}, R_G = 10\Omega$	-	50	-	
Turn - off Delay Time	$t_{d(off)}$	$T_j = 25^\circ\text{C}$	-	120	-	
Fall Time	t_f	Inductive Load	-	47	-	
Turn - on Delay Time	$t_{d(on)}$	$I_C = 40\text{A}, V_{CC} = 400\text{V}$	-	34	-	ns
Rise Time	t_r	$V_{GE} = 15\text{V}, R_G = 10\Omega$	-	50	-	
Turn - off Delay Time	$t_{d(off)}$	$T_j = 175^\circ\text{C}$	-	135	-	
Fall Time	t_f	Inductive Load	-	59	-	
Reverse Bias Safe Operating Area	RBSOA	$I_C = 160\text{A}, V_{CC} = 520\text{V}$ $V_P = 650\text{V}, V_{GE} = 15\text{V}$ $R_G = 60\Omega, T_j = 175^\circ\text{C}$	FULL SQUARE			-

●FRD Electrical Characteristics (at $T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F = 20\text{A}$ $T_j = 25^\circ\text{C}$	-	1.35	1.8	V
		$T_j = 175^\circ\text{C}$	-	1.15	-	
Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}$	-	58	-	ns
Diode Peak Reverse Recovery Current	I_{rr}	$V_{CC} = 400\text{V}$ $di_F/dt = 200\text{A}/\mu\text{s}$	-	6.5	-	A
Diode Reverse Recovery Charge	Q_{rr}	$T_j = 25^\circ\text{C}$	-	0.21	-	μC
Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}$	-	236	-	ns
Diode Peak Reverse Recovery Current	I_{rr}	$V_{CC} = 400\text{V}$ $di_F/dt = 200\text{A}/\mu\text{s}$	-	10.7	-	A
Diode Reverse Recovery Charge	Q_{rr}	$T_j = 175^\circ\text{C}$	-	1.36	-	μC

●Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

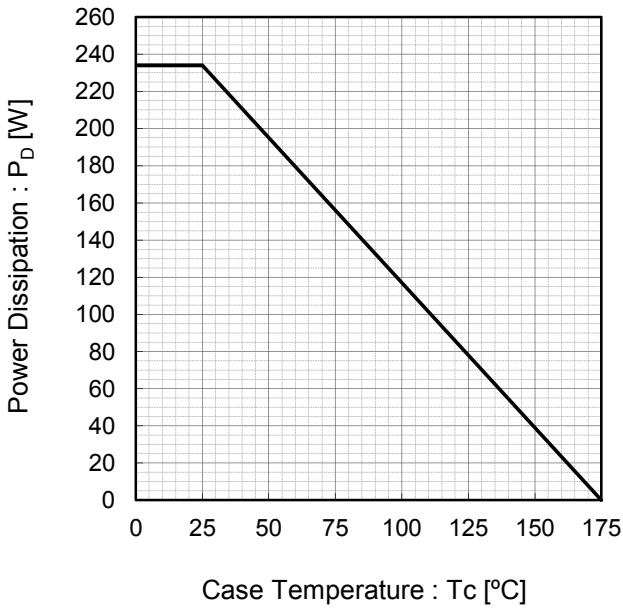


Fig.2 Collector Current vs. Case Temperature

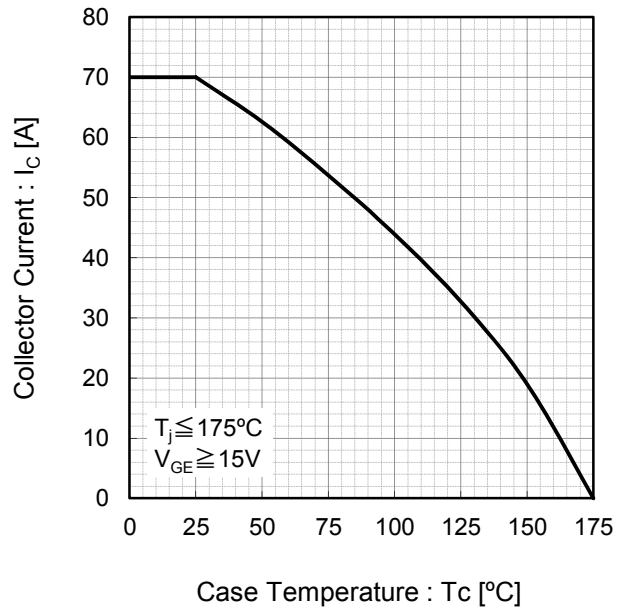


Fig.3 Forward Bias Safe Operating Area

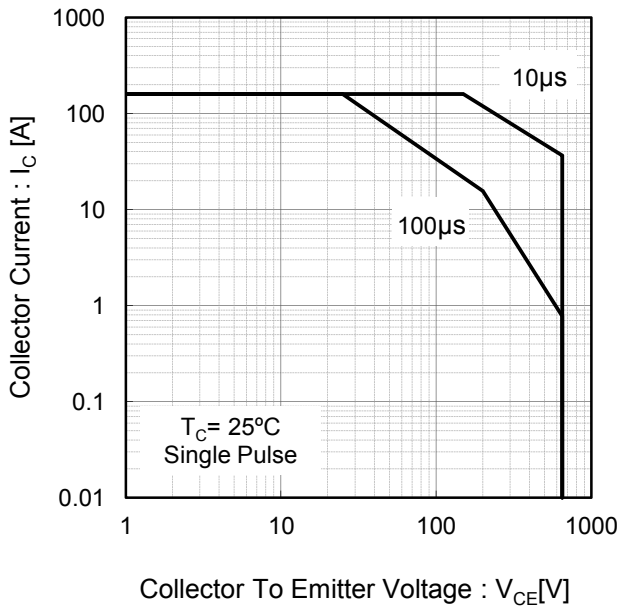
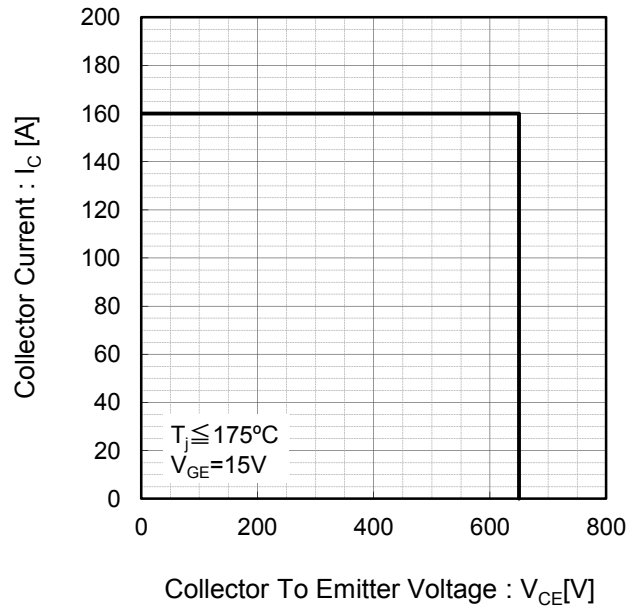


Fig.4 Reverse Bias Safe Operating Area



●Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

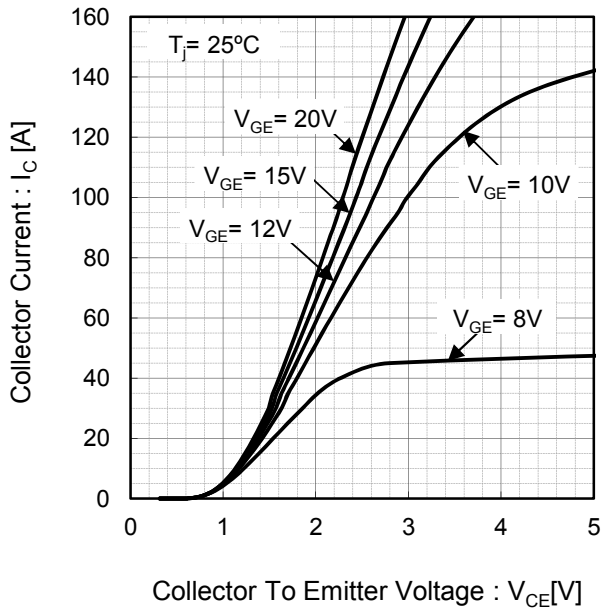


Fig.6 Typical Output Characteristics

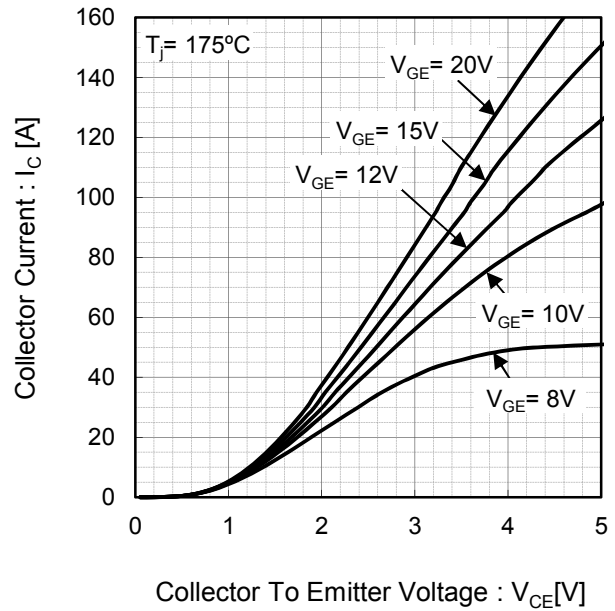


Fig.7 Typical Transfer Characteristics

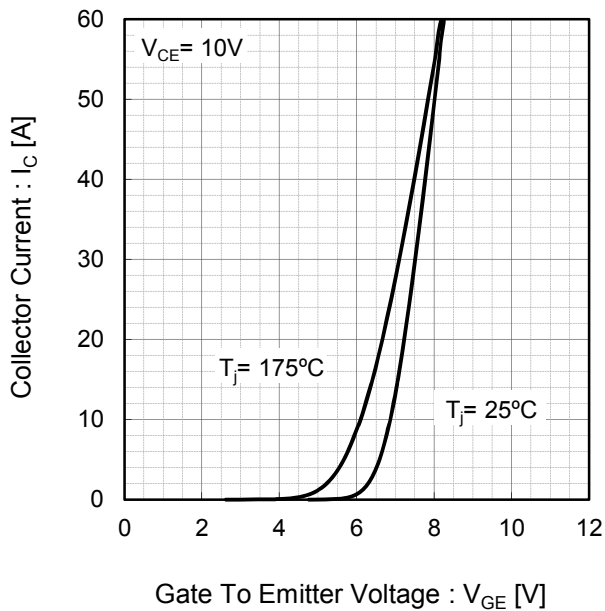
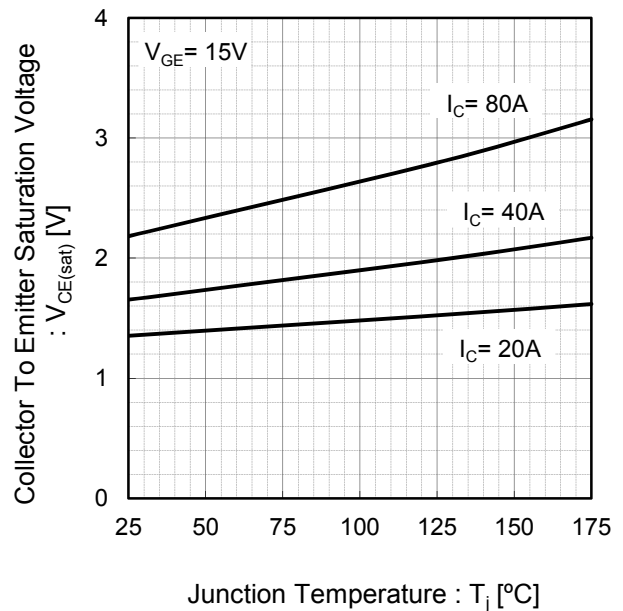


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



●Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

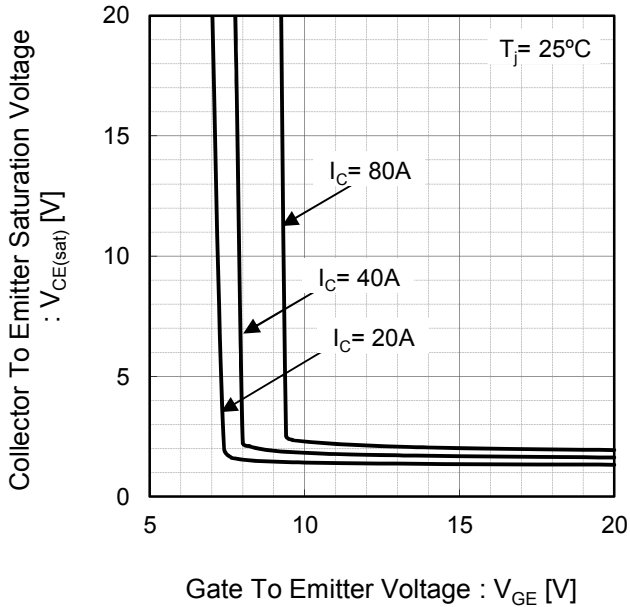


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

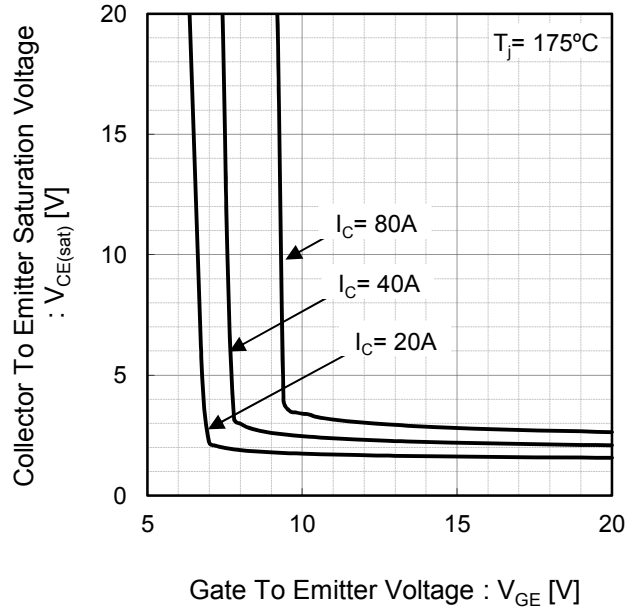


Fig.11 Typical Switching Time vs. Collector Current

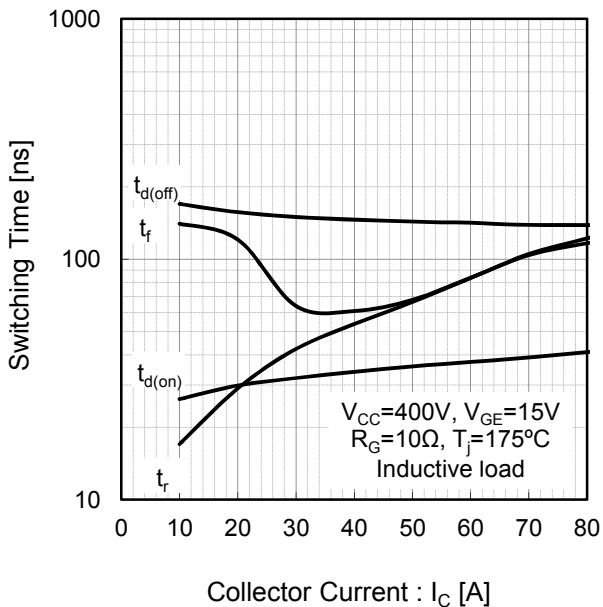
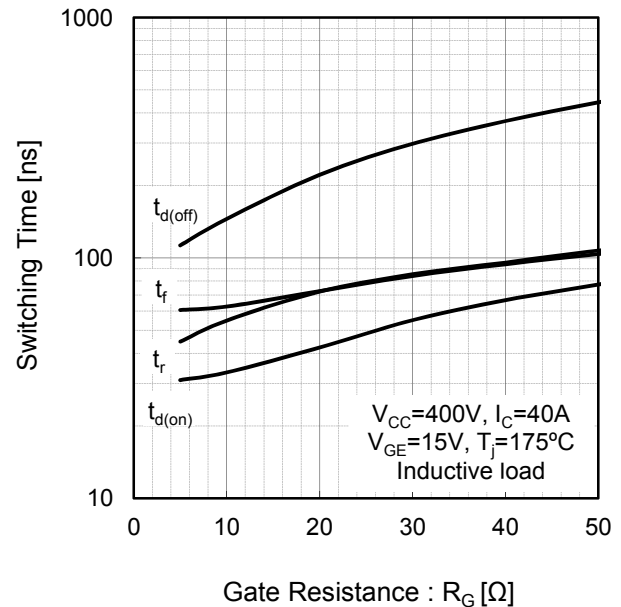


Fig.12 Typical Switching Time vs. Gate Resistance



●Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

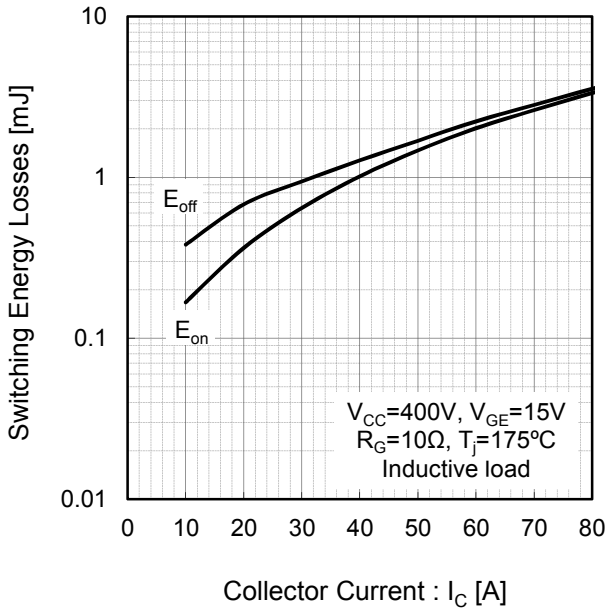


Fig.14 Typical Switching Energy Losses vs. Gate Resistance

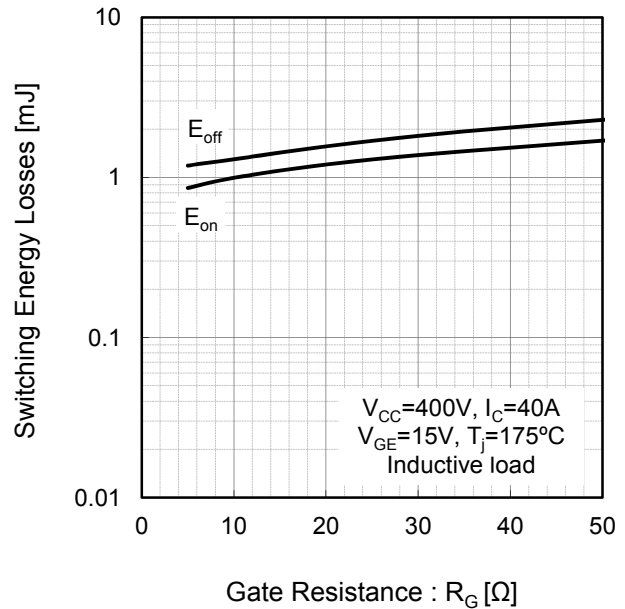


Fig.15 Typical Capacitance vs. Collector To Emitter Voltage

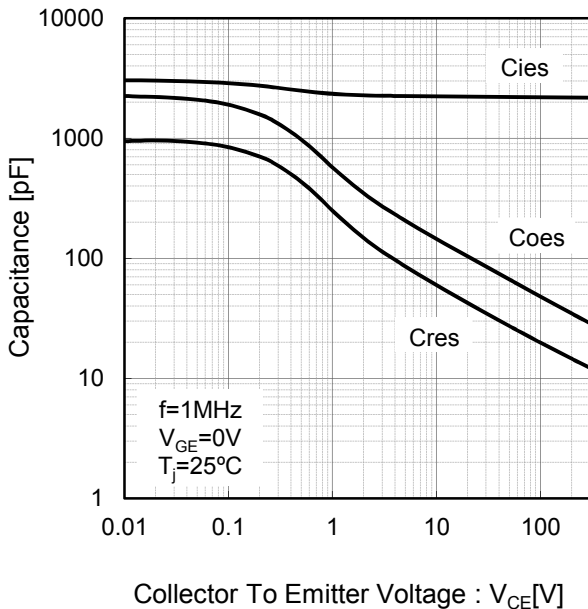
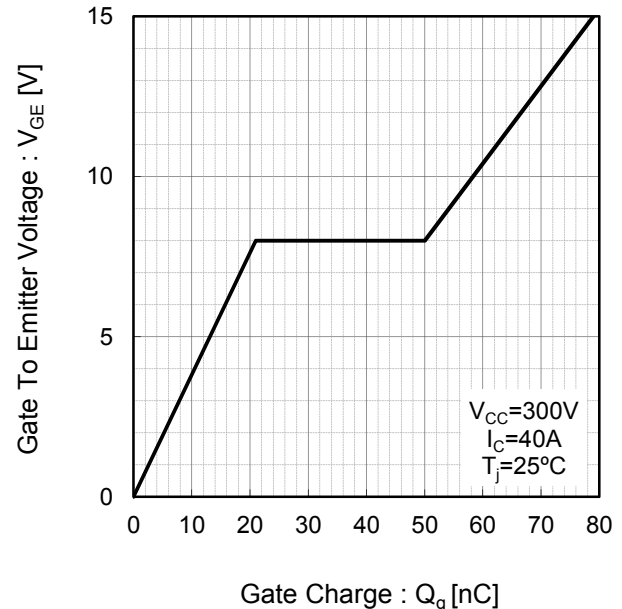


Fig.16 Typical Gate Charge



●Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current vs. Forward Voltage

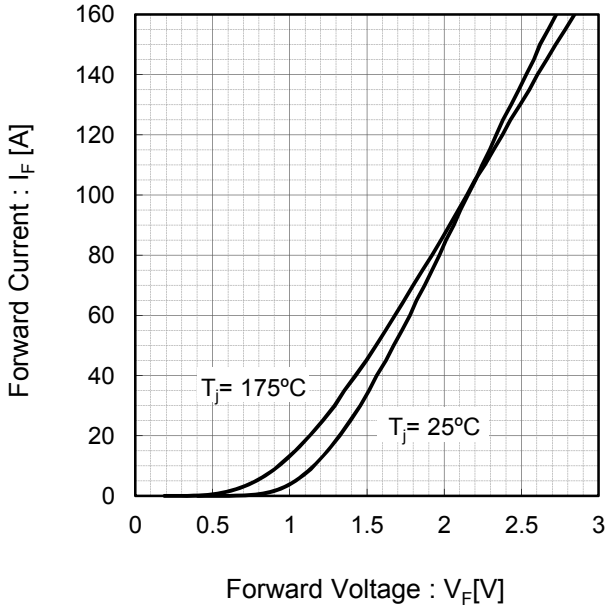


Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current

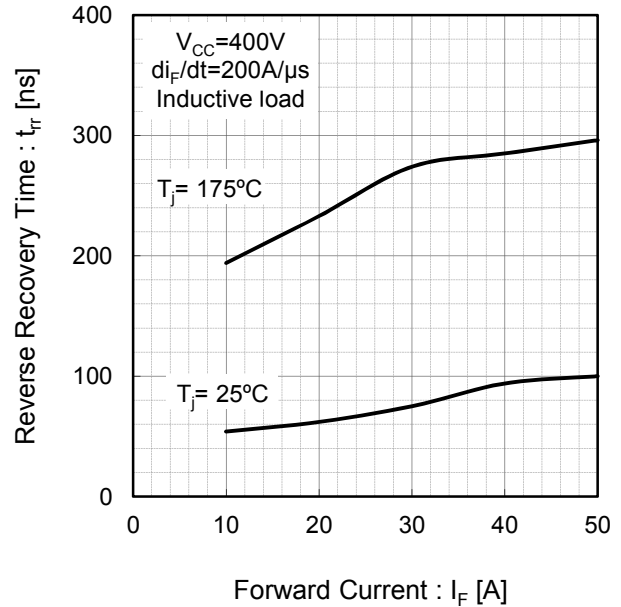


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

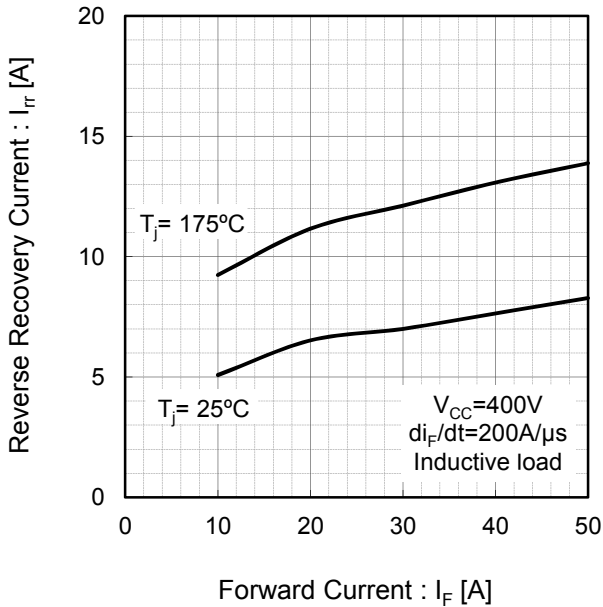
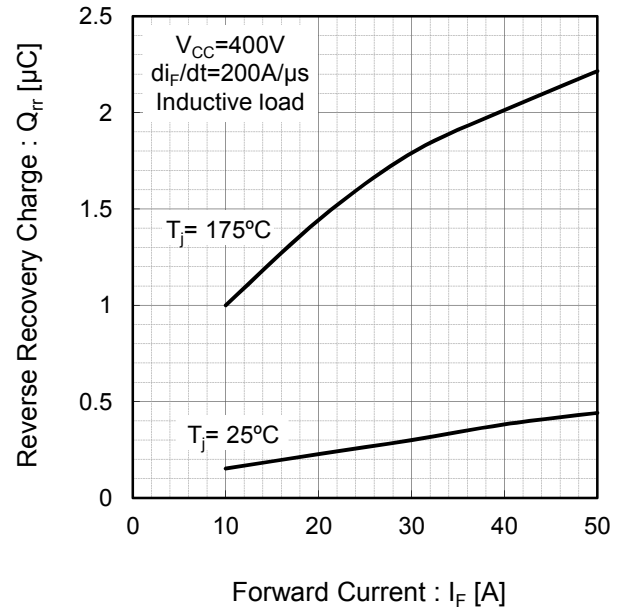


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



●Electrical Characteristic Curves

Fig.21 IGBT Transient Thermal Impedance

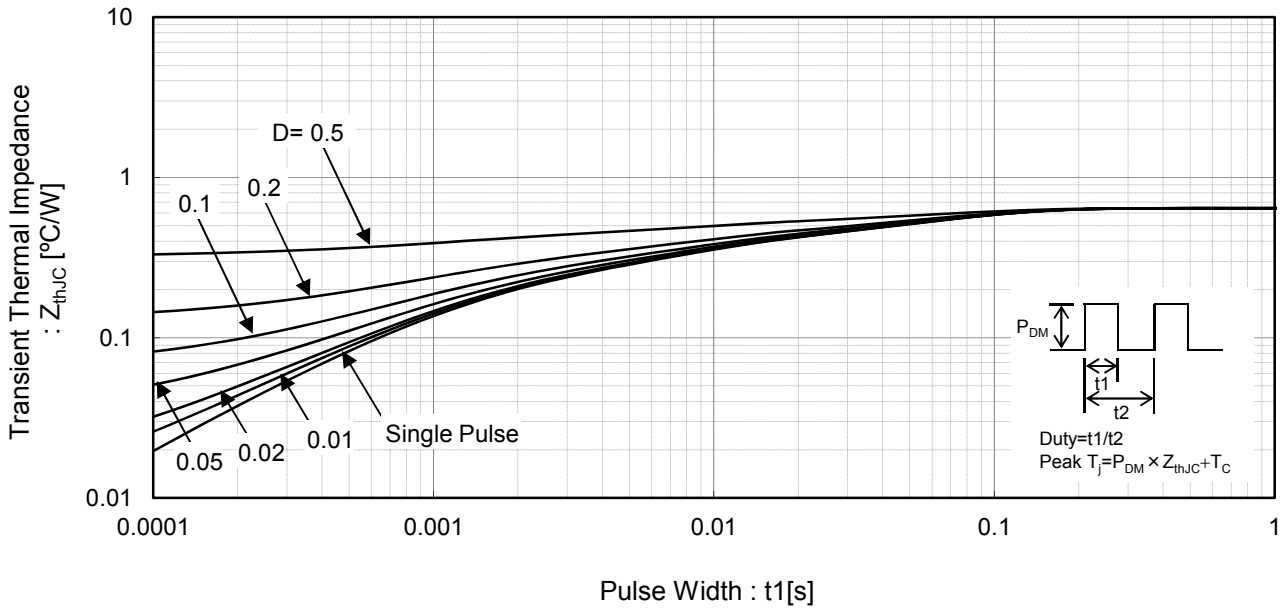
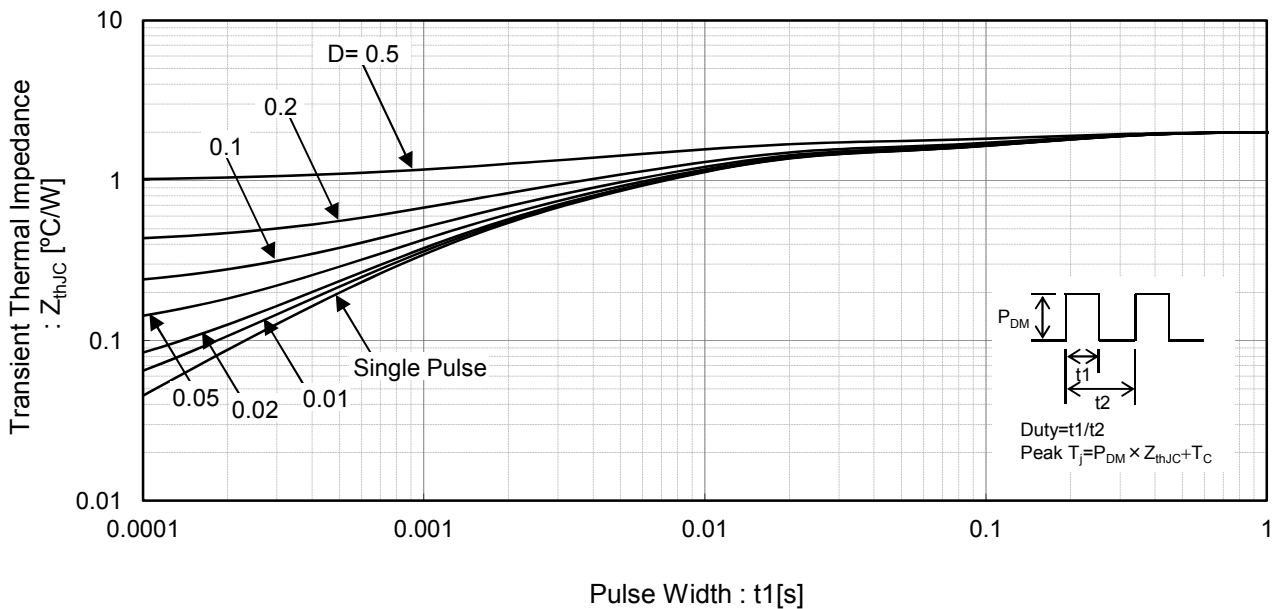


Fig.22 Diode Transient Thermal Impedance



● Inductive Load Switching Circuit and Waveform



Fig.23 Inductive Load Circuit

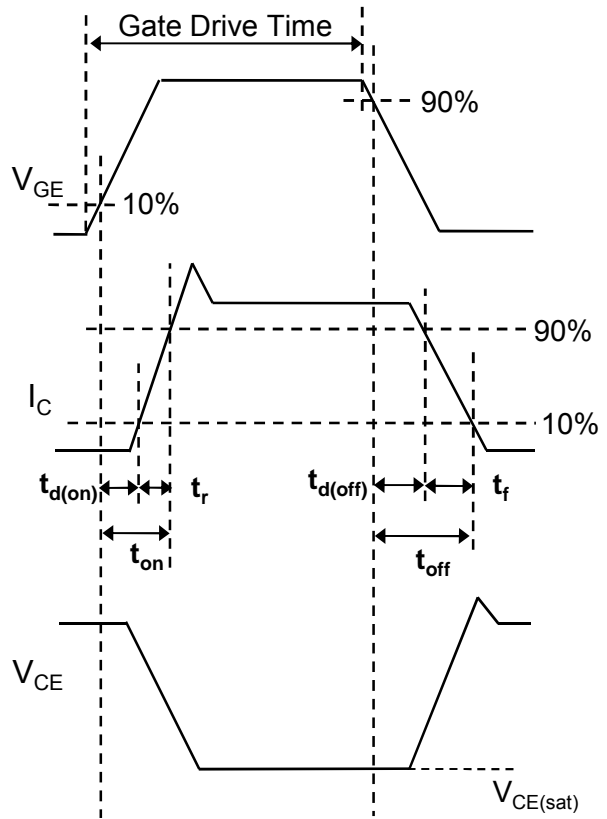


Fig.24 Inductive Load Waveform

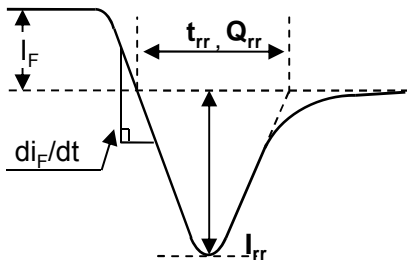


Fig.25 Diode Reverse Recovery Waveform

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RGTH80TS65D - Web Page

[Distribution Inventory](#)

Part Number	RGTH80TS65D
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	450
Packing Type	Bulk
Constitution Materials List	inquiry
RoHS	Yes

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